Abstracts

High performance circuits in 0.18 /spl mu/m SiGe BiCMOS process for wireless applications (2002 Vol. I [MWSYM])

Peihua Ye, B. Agarwal, M. Reddy, L. Li, J. Cheng, P.C. Mudge, E. McCarthy and S.L. Lloyd. "High performance circuits in 0.18 /spl mu/m SiGe BiCMOS process for wireless applications (2002 Vol. I [MWSYM])." 2002 MTT-S International Microwave Symposium Digest 02.1 (2002 Vol. I [MWSYM]): 175-178 vol.1.

Silicon germanium bipolar CMOS (SiGe BiCMOS) process technology is gaining increasing popularity for RF circuits in wireless applications due to high performance, low cost, high yield and higher levels of integration with mixed signal and digital CMOS circuits. Four test circuits were designed and fabricated in Conexant's 0.18 /spl mu/m SiGe BiCMOS process to evaluate the performance benefits provided by this state of the art process technology. The RF performance achieved in this process clearly makes this a process of choice for future RFIC products.

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